HMPD260R100

Pad Information	Project	Size(um)
	Chip X (in S/L)	1390
	Chip Y (in S/L)	820
	Scribe line	60
	AX	140
	AY	140
	C	1245
	D	675
	E	535
	F	1100
	G	72.5

Die Size	1390 um X 820 um (with S/L)
Gross Die	25000EA
Wafer Diameter	200 mm
Wafer Thickness	6 mil ± 0.5 mil
Material of Electrode	Front : Al (Thickness : 45 KÅ ± 3 KÅ)
	Back : Ti-Ni-Ag
Width of Scribe Line	60um

Symbol | Die Outline

3, Electrical Characteristics (Ta = 25 ºC Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-100	V
V_{GSS}	Gate-Source Voltage	±20	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_{DS} = -250 μA	-1.3	-1.8	-2.5	V
I_{DSS}	Drain Leakage Current	V_{DS} = -100 V, V_{GS} = 0 V	–	–	-1	μA
I_{GSS}	Gate Leakage Current	V_{GS} = ± 20 V, V_{DS} = 0 V	–	–	± 100	nA
$R_{DS(ON)}$②	On-State Resistance	V_{GS} = -10 V, I_{DS} = -1 A		260	320	mΩ
		V_{GS} = -4.5 V, I_{DS} = -1 A		290	380	mΩ
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{SD} = -0.5 A, V_{GS} = 0 V	-	-0.7	-1.3	V

Notes: ① This characteristics assumes the die are assembled in SOT23 packages. Actual performance may degrade when assembled.

②CP measured on wafer by probe card.